

MvpLED™ SL-V-G40AC

High Power Green LED

Green LED

Introduction

The advantages of the patented and proprietary MvpLED™ design especially in Thermal management, and Optical efficacy, are realized in light quality, lifetime, color consistency, reliability and overall efficiency of the luminaire. Available in UV, Violet, Blue and Green, SemiLEDs high efficiency chips bring real benefits to any lamp or luminaire manufacturer.

Copper alloy, used in SemiLEDs MvpLED™ chips, is a better conductor of heat than any other material on the market used in the fabrication of LEDs. This is a major advantage for any lamp or luminaire manufacturer. No matter how good a thermal design is, if the contact material to the junction is a poor conductor then the cooling effects of the heat-sink are significantly reduced.

Using a proprietary surface texturing technique, SemiLEDs LEDs maximize light extraction and efficiency. Coupled with the lack of Sapphire and a 90% efficient Reflective Layer, SemiLEDs chips exhibit an almost perfect Lambertian radiation pattern.

SemiLEDs' patented and unique process consumes no Sapphire, significantly reducing the Carbon footprint. The lack of a Sapphire base also removes a thermal management bottleneck while providing the most environmentally friendly LED on the market.

RoHS and REACH Compliant

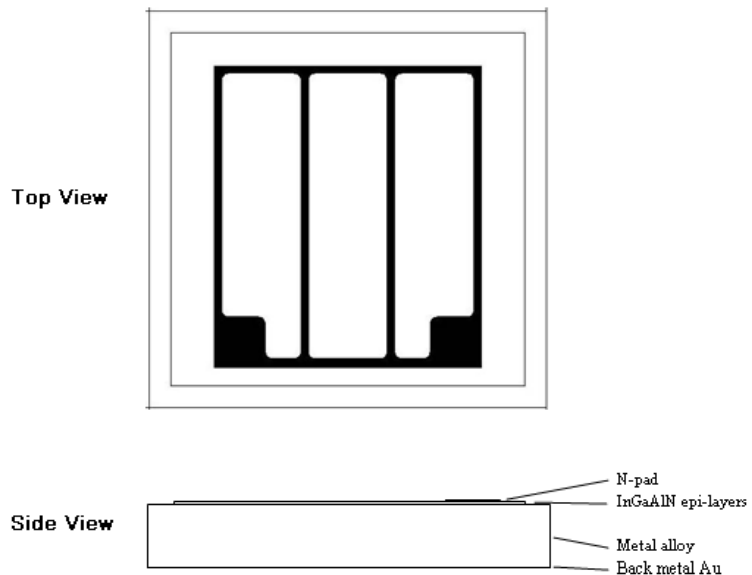
Feature

Metal alloy device	Low cost high thermal conductivity
Thickness 145 μm	Less thermal distance
P-N junction high at 140 μm	Silver epoxy die attachment compatible
One pad structure	Low package cost
Nearly Perfect Lambertian emission pattern	Ideal for white light design
Patterned surface	Maximum light extraction

Applications

LCD backlight
 Architecture lighting
 High Power LED
 Entertainment lighting
 Signalling
 Signage
 Light Engine
 Landscape

Chip Mechanical Diagram



Mechanical Specifications

P-N junction area	970 μm X 970 μm	$\pm 20 \mu\text{m}$
Base area	1070 μm X 1070 μm	$\pm 50 \mu\text{m}$
Chip thickness	145 μm	$\pm 15 \mu\text{m}$
Bond pad size	140 μm	$\pm 15 \mu\text{m}$
Bond pad thickness	2.5 μm	$\pm 0.5 \mu\text{m}$
Junction height	140 μm	$\pm 15 \mu\text{m}$

Optical and Electrical Characteristics at 350mA, Ta at 25°C

Parameter	Symbol	Min	Typ	Max	Remark
Forward voltage:	Vf		3.3	3.6	Volt
Spectra half width	$\Delta\lambda$		35	50	nm
Reverse current	Ir			2 μ A	Vr= 5 Volt

Measured by SemiLEDs on bare chip

Absolute Maximum Ratings, Ta at 25°C

Forward Current (DC)	500 mA
Peak Forward Current (1/10 duty cycle @ 1KHz)	800 mA
LED Junction Temperature	125°C
Reverse Voltage	5 V
Operating Temperature	-40°C to +110°C
Storage Temperature	-40°C to +110°C
Temperature during packaging (reflow)	280°C < 10 sec

Maximum ratings are strongly package dependent and may differ between different packaged devices. The values given were collected by SemiLEDs' in-house package.

BIN Table (Output Power at 350mA, Ta at 25°C)

Wd Range (nm)	10-12cd	12-14cd	14-16cd	16-18cd	18-20cd	20cd up
500-505	CA	CB	CC	CD		
505-510	DA	DB	DC	DD	DE	
510-515	EA	EB	EC	ED	EE	EF
515-520	FA	FB	FC	FD	FE	FF
520-525	GA	GB	GC	GD	GE	GF
525-530	HA	HB	HC	HD	HE	
530-535	IA	IB	IC	ID	IE	

Performance Diagram

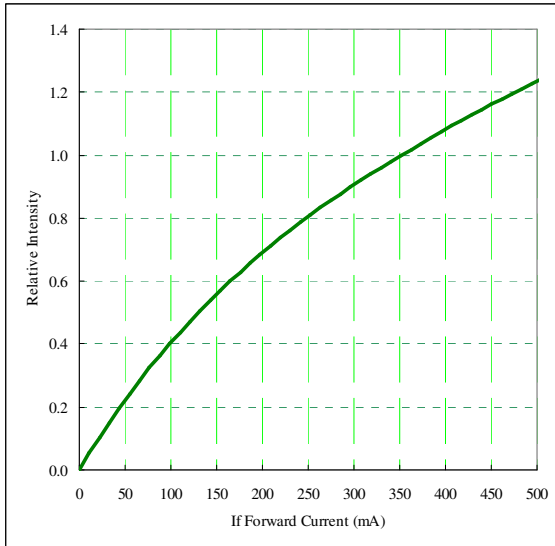


Fig-1 Relative Intensity vs. Forward Current.

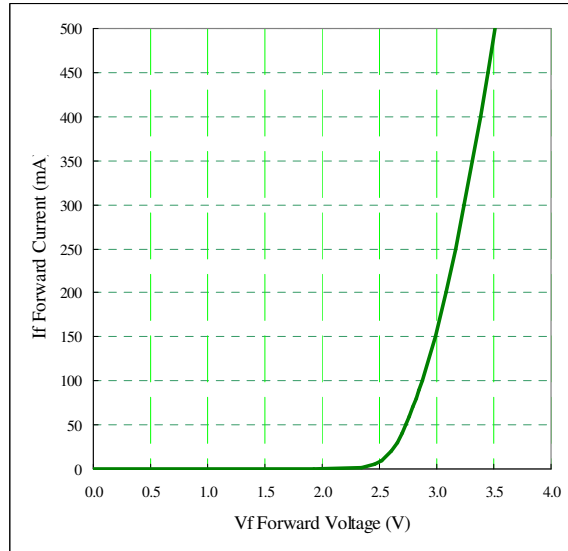


Fig-2 Forward Current vs. Forward Voltage.

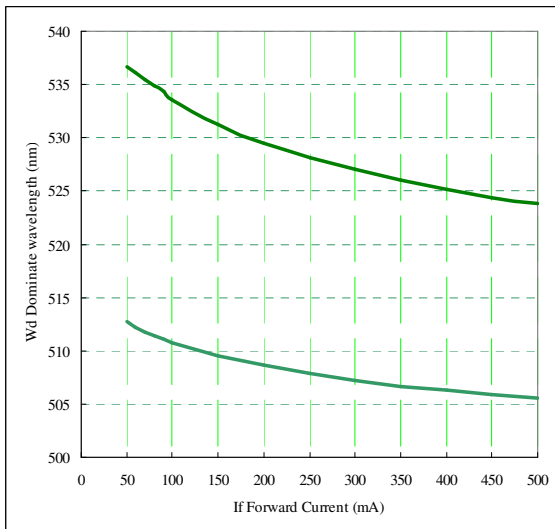


Fig-3 Forward Dominate Wavelength vs. Forward Current.

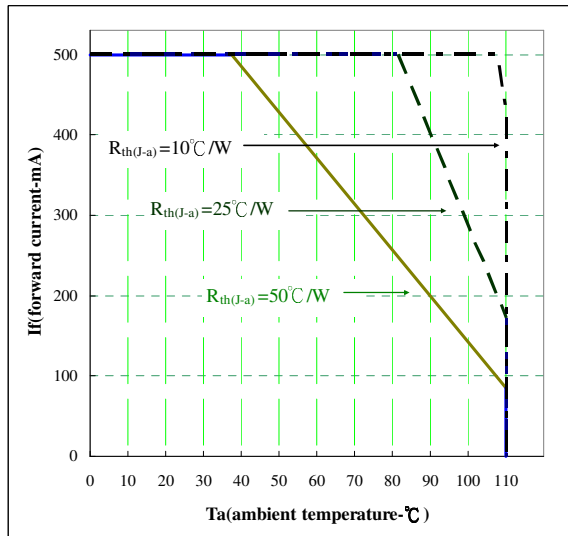


Fig-4 Maximum Driving Forward DC Current vs. Ambient Temperature.

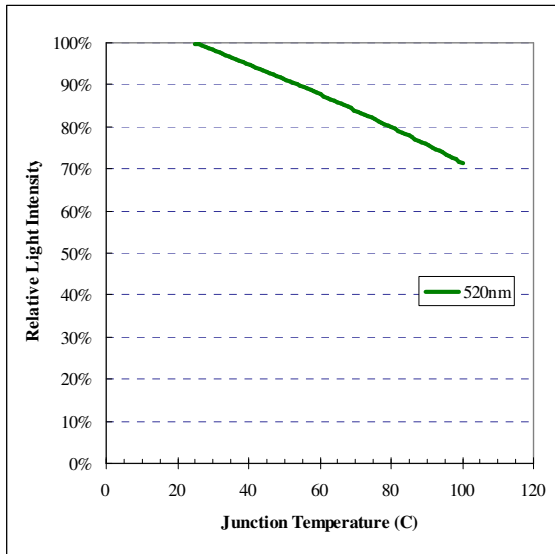


Fig-5 Relative Intensity vs. Junction Temperature.

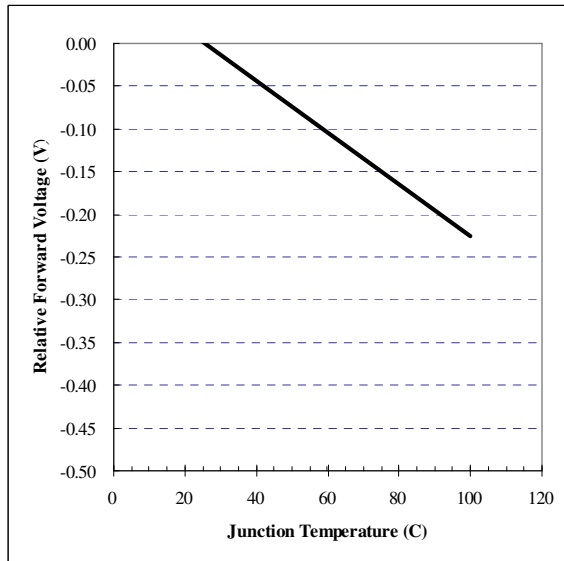


Fig-6 Relative Forward Voltage vs. Junction Temperature.

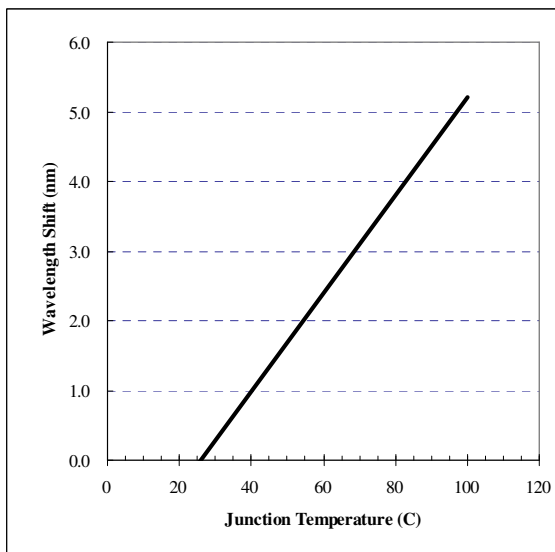


Fig-7 Wavelength Shift vs. Junction Temperature.

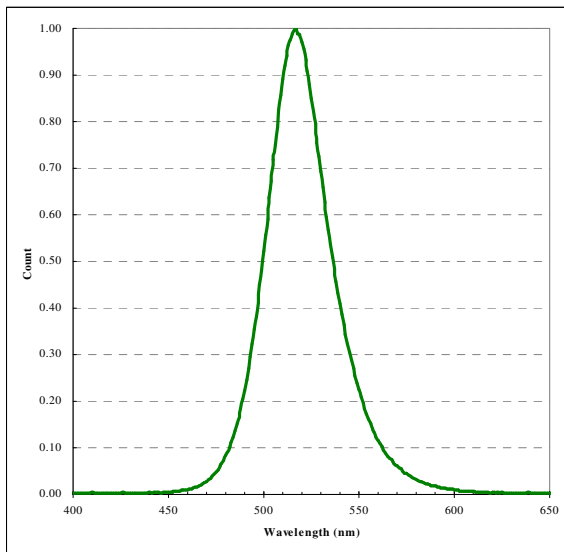


Fig-8 Relative Intensity vs. Peak Wavelength.

Note:

- Minimum and maximum value refers to the limits and set up of SemiLEDs' testers. All other measurement data are defined as long-term production mean values and are only given for information.
- A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system. Life support devices or systems are intended (i) to be implanted in the human body, or (ii) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered. Components used as a critical component must be approved in writing by SemiLEDs.

About Us

SemiLEDs is a US based manufacturer of ultra-high bright LED chips with state of the art fabrication facilities in Hsinchu Science Park, Taiwan. SemiLEDs specializes in the development and manufacturing of metal alloy vertical LED chips in blue (white), green and UV using our patented and proprietary MvpLED™ technology. This unique design allows for higher performance and longer lumen maintenance. SemiLEDs new high power I-core MvpLEDs™ can deliver over 120lm/W. In December 2008 The World Economic Forum recognized SemiLEDs innovations with the 2009 Technology Pioneer Award.



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